

30V Single N-Channel Enhancement-Mode MOSFET

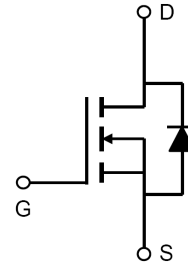
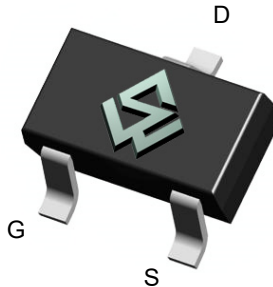
General Description

- Low gate charge.
- Use as a load switch.
- Use in PWM applications

Product Summary

- BV_{DSS} 30V
- $R_{DS(on)}$ @ $V_{GS} = 10V$ < 28m Ω (Typ.:20 m Ω)
- $R_{DS(on)}$ @ $V_{GS} = 4.5V$ < 32m Ω (Typ.:24 m Ω)
- $R_{DS(on)}$ @ $V_{GS} = 2.5V$ < 50m Ω (Typ.:34 m Ω)

SOT23-3L



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Current (Using<10s, $T_C < 25^\circ\text{C}$)	I_{DC}	5.8	A
Continuous Current (Using<10s, $T_C < 100^\circ\text{C}$)		4.7	A
Drain Current ($T_A = 25^\circ\text{C}$, $V_{GS} = 10V$, $T_C < 160^\circ\text{C}$)	I_D	4.2	A
Drain Current ($T_A = 75^\circ\text{C}$, $V_{GS} = 10V$, $T_C < 160^\circ\text{C}$)		3.8	A
Pulsed Drain Current ^a	I_{DM}	20	A
Power Dissipation ^b ($T_A = 25^\circ\text{C}$)	P_D	1.4	W
Power Dissipation ^b ($T_A = 75^\circ\text{C}$)		1.0	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	$^\circ\text{C}$

Thermal Characteristics

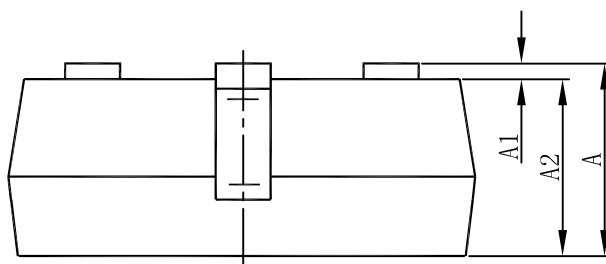
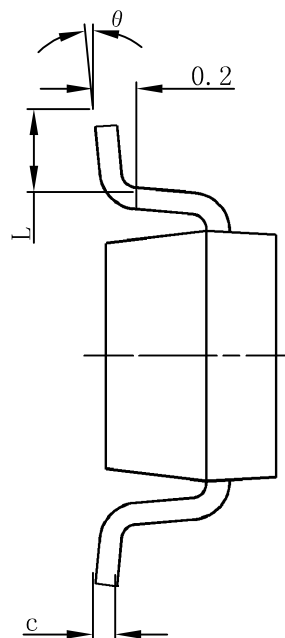
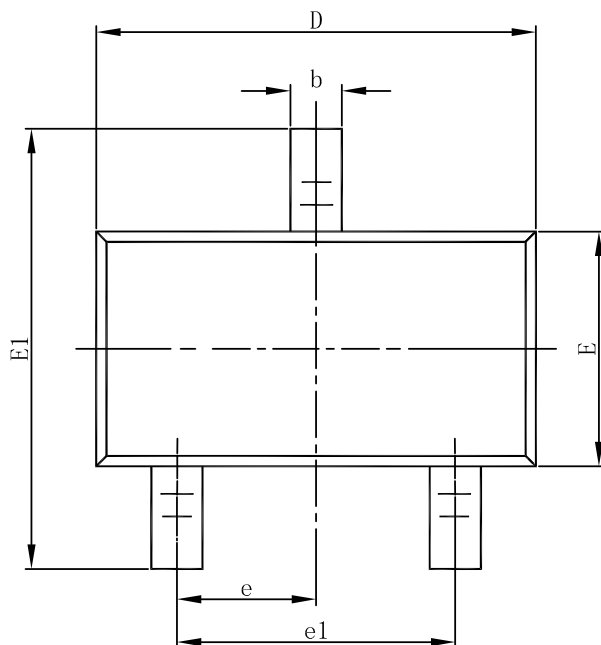
Parameter	Symbol	Maximum	Units
Junction-to-Ambient ^a ($t \leq 10s$)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Junction-to-Ambient ^{a,d} (Steady-State)		130	$^\circ\text{C/W}$
Junction-to-Lead (Steady-State)	$R_{\theta JL}$	90	$^\circ\text{C/W}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 30V, V_{GS} = 0V$			1	μA
I_{GSS}	Gate-Body Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.6	0.9	1.4	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 5.8A$		20	28	m Ω
		$V_{GS} = 4.5V, I_D = 4.5A$		24	32	m Ω
		$V_{GS} = 2.5V, I_D = 2.5A$		34	50	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = 2.5V, I_D = 5.8A$		20		S
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = 1.0A$			1.2	V
I_S	Maximum Body-Diode Continuous Current				2.0	A
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V$ $f = 1.0MHz$		860		pF
C_{oss}	Output Capacitance			63		pF
C_{rss}	Reverse Transfer Capacitance			54		pF
Q_g	Total Gate Charge	$V_{DS} = 15V, I_D = 5.8A$ $V_{GS} = 6V$		8.5		nC
Q_{gs}	Gate-Source Charge			2.1		nC
Q_{gd}	Gate-Drain Charge			2.6		nC
$t_{D(ON)}$	Turn-On Delay Time	$V_{DD} = 15V, I_D = 1A$ $V_{GS} = 6V$ $R_{GEN} = 6\text{ ohm}$		4		ns
t_r	Turn-On Rise Time			3.2		ns
$t_{D(OFF)}$	Turn-Off Delay Time			28		ns
t_f	Turn-Off Fall Time			6		ns

- Repetitive rating, Pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and duty cycles to keep initial $T_J=25^\circ\text{C}$
- The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using $\leq 10s$ junction-to-ambient thermal resistance.
- The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$. The value in any given application depends on the user's specific board design.
- The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

SOT23-3L Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°